



SANYO Semiconductors

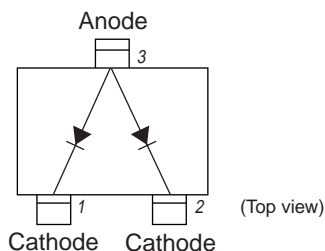
DATA SHEET

DCA010 — Silicon Epitaxial Planar Type (Anode Common) Very High-Speed Switching Diode

Features

- Ideally suited for use in hybrid ICs because of very small-sized package.
- Fast switching speed.
- Small interterminal capacitance.

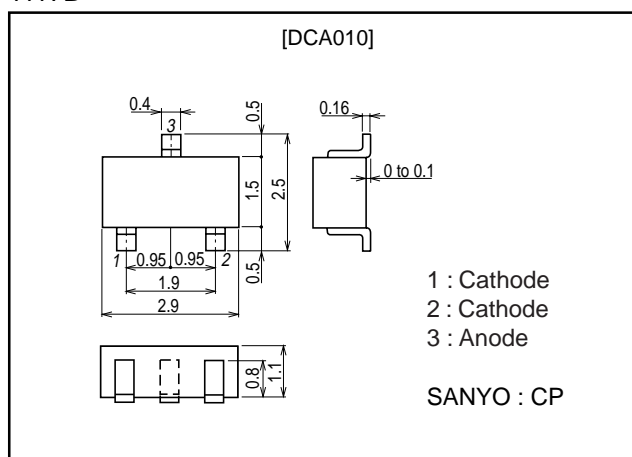
Electrical Connection



Package Dimensions

unit : mm

1117B



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Peak Reverse Voltage	V_{RM}		85	V
Reverse Voltage	V_R		80	V
Peak Forward Current	I_{FM}	Unit rating	300	mA
		Total rating	450	mA
Average Rectified Current	I_O	Unit rating	100	mA
		Total rating	150	mA
Surge Current (1μs)	I_{FSM}	Unit rating	4	A
		Total rating	6	A
Allowable Power Dissipation	P		200	mW
Junction Temperature	T_J		125	°C
Storage Temperature	T_{stg}		-55 to +125	°C

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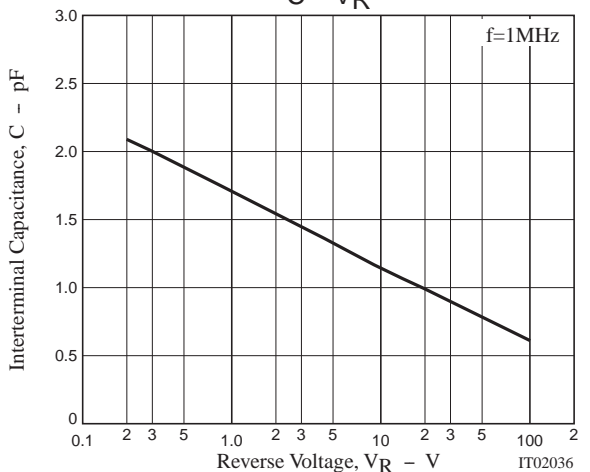
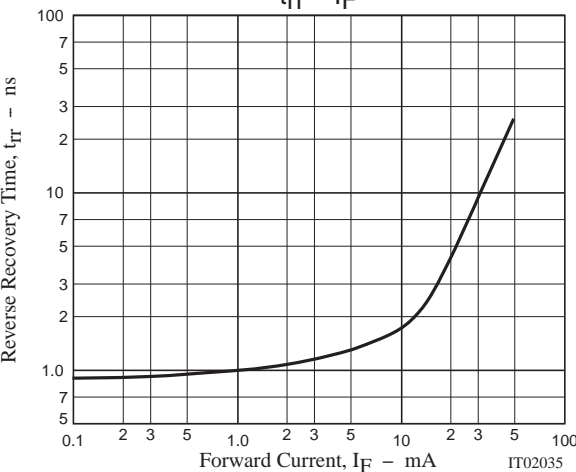
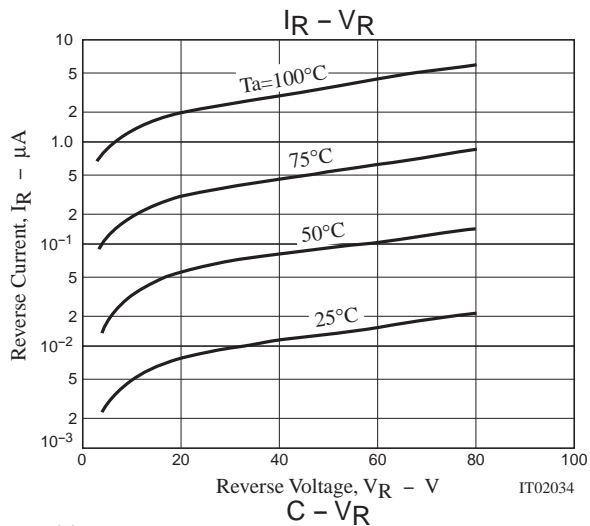
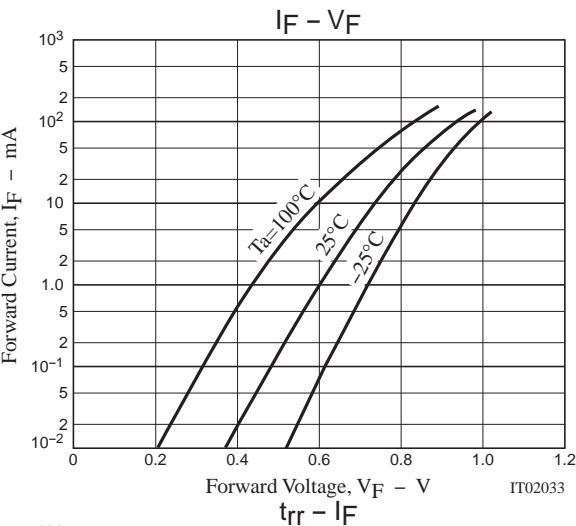
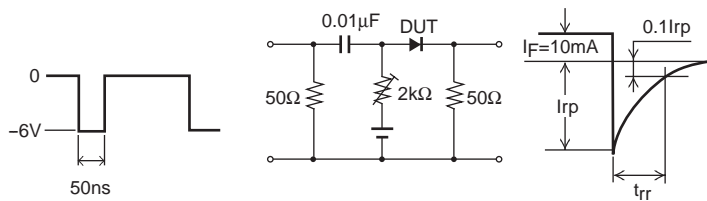
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward Voltage	V _{F1}	I _F =1mA		0.61		V
	V _{F2}	I _F =10mA		0.74		V
	V _{F3}	I _F =100mA			1.20	V
Reverse Current	I _{R1}	V _R =30V			0.1	μA
	I _{R2}	V _R =80V			0.5	μA
Interterminal Capacitance	C	V _R =0, f=1MHz			4.0	pF
Reverse Recovery Time	t _{rr}	I _F =10mA, V _R =6V, R _L =50Ω, I _{rr} =0.1I _{rp}			4.0	ns

Marking : W5

Reverse Recovery Time Test Circuit



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